

1SS119

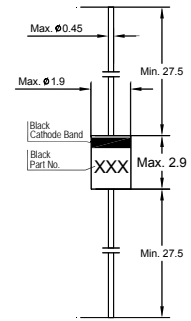
Silicon Epitaxial Planar Switching Diode

Features

- Low capacitance
- Short reverse recovery time

Applications

- High-speed switching



Glass Case DO-34
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	35	V
Reverse Voltage	V_R	30	V
Average Rectified Forward Current	$I_{F(AV)}$	150	mA
Peak Forward Current	I_{FM}	450	mA
Non-Repetitive Peak Forward Surge Current ($t = 1\text{ s}$)	I_{FSM}	1	A
Power Dissipation	P_{tot}	250	mW
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 175	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	V_F	0.8	V
Reverse Current at $V_R = 30\text{ V}$	I_R	0.1	μA
Total Capacitance at $V_R = 1\text{ V}$, $f = 1\text{ MHz}$	C_{tot}	3	pF
Reverse Recovery Time at $I_F = 10\text{ mA}$, $V_R = 6\text{ V}$, $R_L = 50\ \Omega$	t_{rr}	3.5	ns

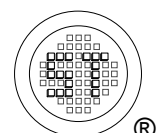


Fig.1-Forward current Vs. Forward voltage

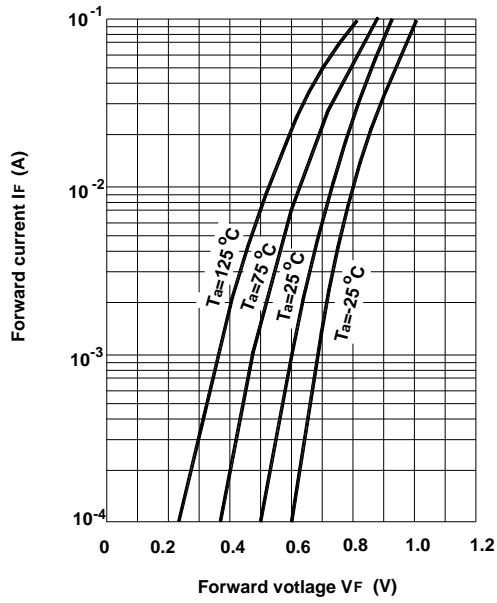


Fig.2- Reverse current Vs. Reverse voltage

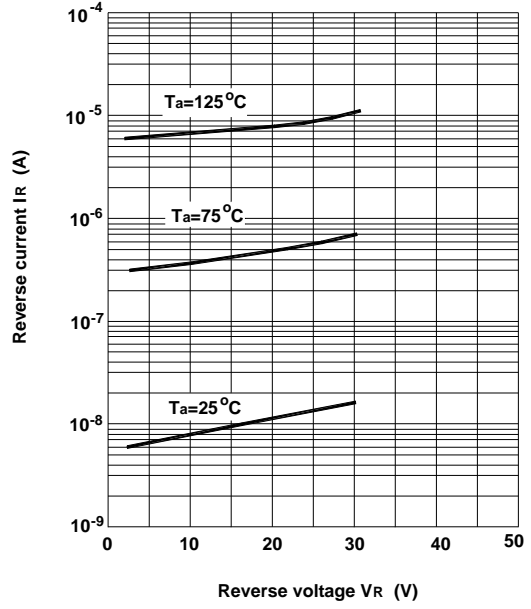


Fig.3- Capacitance Vs. Reverse voltage

